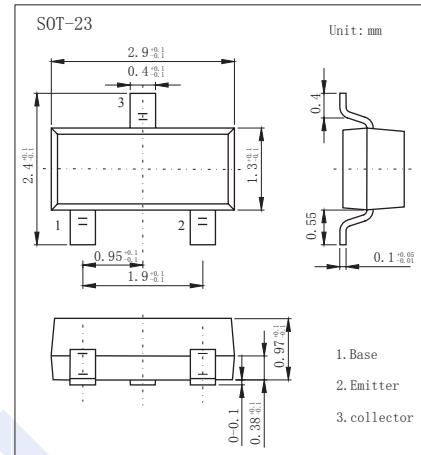


NPN Transistors

2SC3120

■ Features

- Collector Current Capability $I_C=50\text{mA}$
- Collector Emitter Voltage $V_{CEO}=15\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	30	V
Collector - Emitter Voltage	V_{CE0}	15	
Emitter - Base Voltage	V_{EB0}	3	
Collector Current - Continuous	I_C	50	mA
Base Current	I_B	25	
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100\ \mu\text{A}$, $I_E = 0$	30			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1\ \text{mA}$, $I_B = 0$	15			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\ \mu\text{A}$, $I_C = 0$	3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 30\ \text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 2\ \text{V}$, $I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\ \text{mA}$, $I_B = 5\ \text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50\ \text{mA}$, $I_B = 5\ \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 5\ \text{mA}$	40		200	
Conversion gain	G_{ce}	$V_{CC} = 10\ \text{V}$, $I_C = 2\ \text{mA}$, $f = 800\ \text{MHz}$	12			dB
Noise figure	NF	$f_L = 830\ \text{MHz}$ (0dBm)		8		
Reverse current capacitance	C_{re}	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$			0.9	pF
Transition frequency	f_T	$V_{CE} = 10\ \text{V}$, $I_C = 2\ \text{mA}$	1.5			GHz

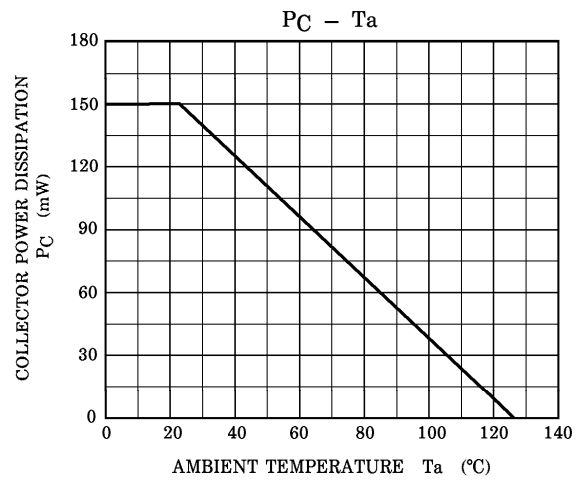
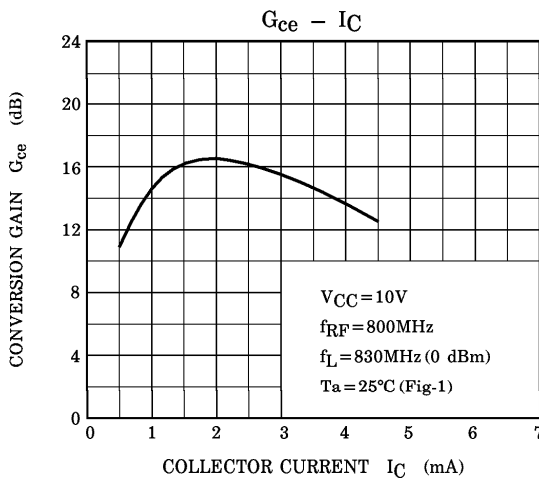
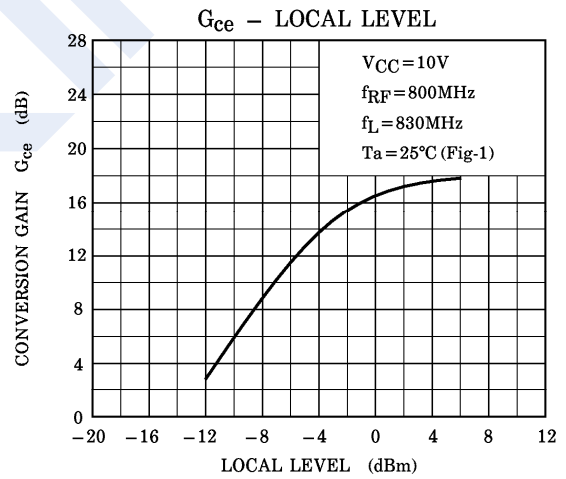
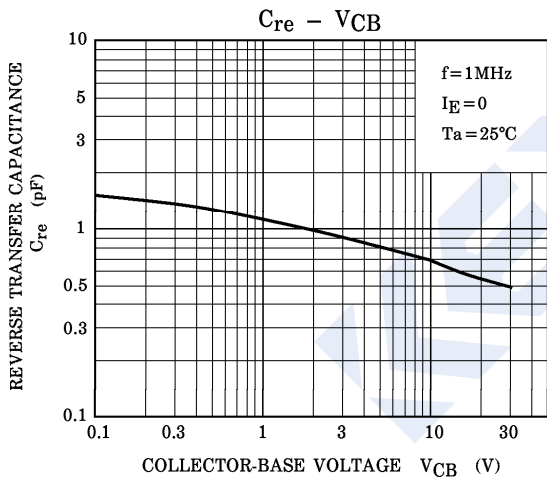
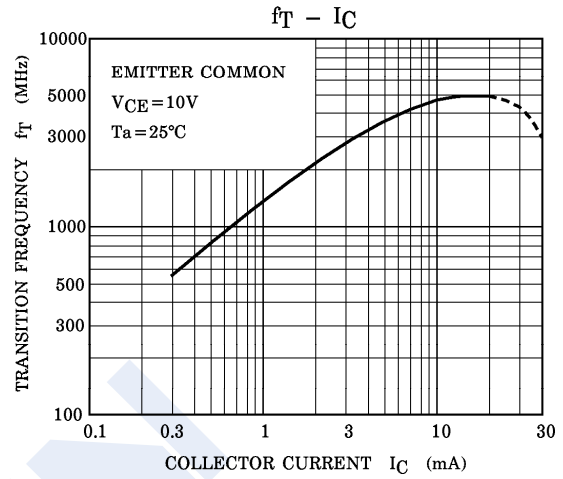
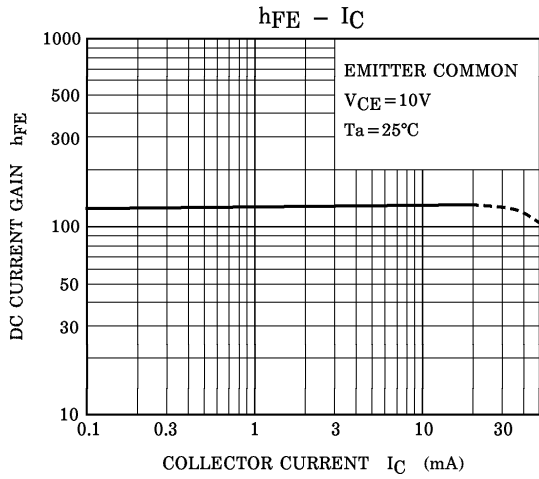
■ Marking

Marking	HB
---------	----

NPN Transistors

2SC3120

■ Typical Characteristics

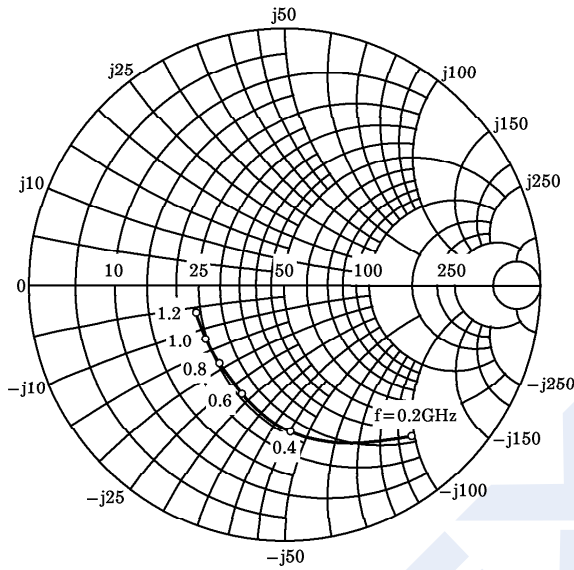


NPN Transistors

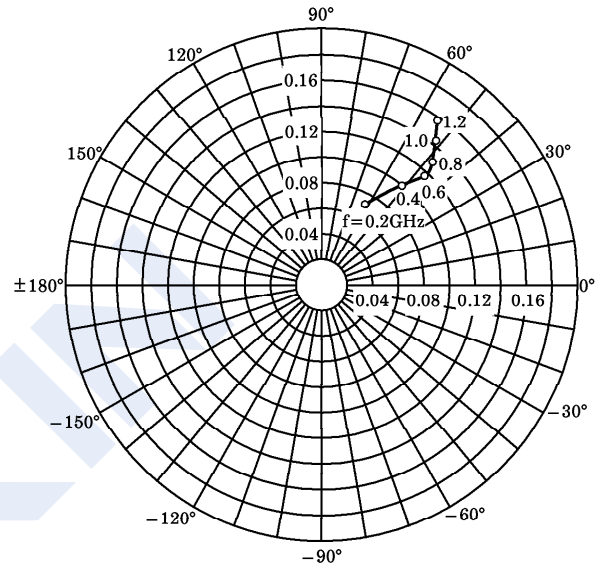
2SC3120

■ Typical Characteristics

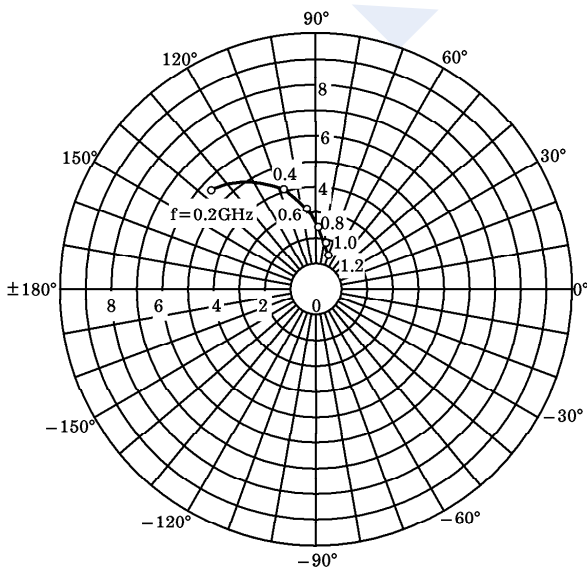
S_{11e}
 $V_{CE} = 10V$
 $I_C = 2mA$
 $T_a = 25^\circ C$
 (UNIT : Ω)



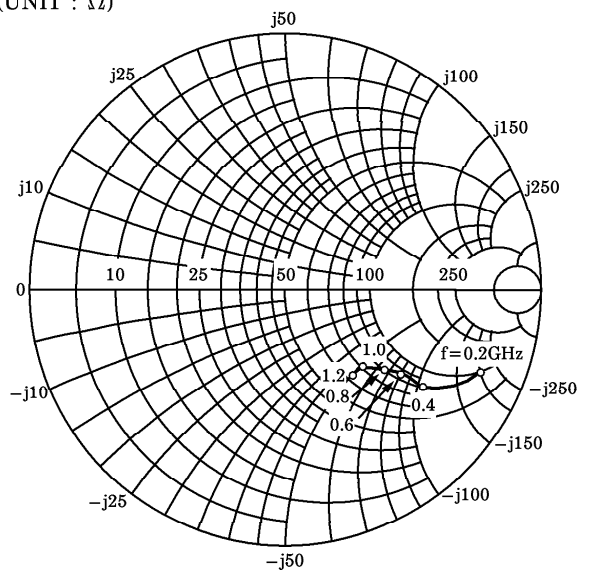
S_{12e}
 $V_{CE} = 10V$
 $I_C = 2mA$
 $T_a = 25^\circ C$



S_{21e}
 $V_{CE} = 10V$
 $I_C = 2mA$
 $T_a = 25^\circ C$



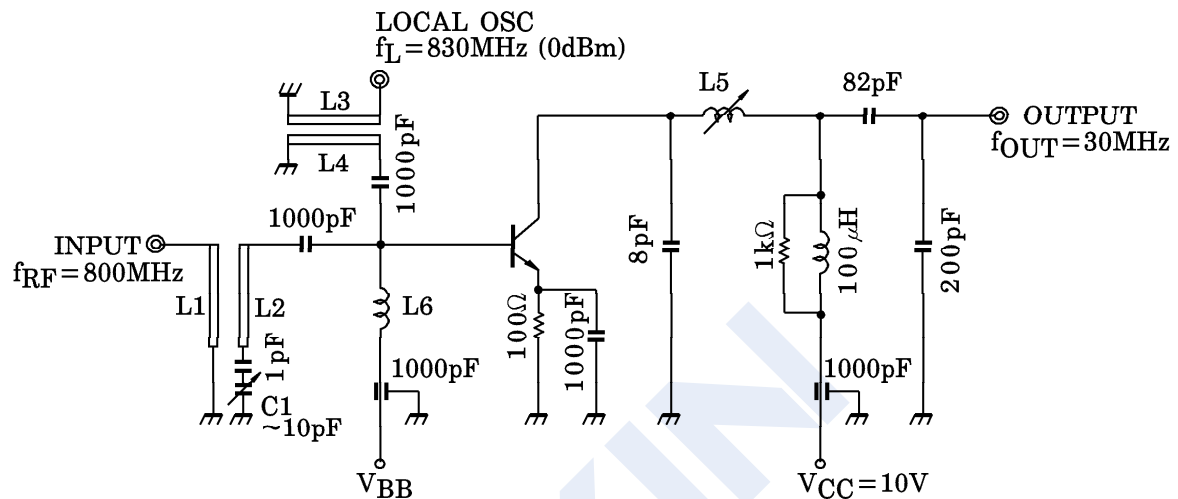
S_{22e}
 $V_{CE} = 10V$
 $I_C = 2mA$
 $T_a = 25^\circ C$
 (UNIT : Ω)



NPN Transistors

2SC3120

■ Typical Characteristics

Fig.1 800MHz G_{ce} , NF TEST CIRCUIT

- L1~L4 : $\phi 0.8\text{mm}$ SILVER PLATED COPPER WIRE
 L5 : AIR COIL SCN-5948 ① - ③ TOKO OR EQUIVALENT
 L6 : $\phi 0.2\text{mm}$ COPPER WIRE 10T 5mm ID
 C1 : AIR TRIMMER TTA23A100 MURATA MFC. Co., LTD. OR EQUIVALENT